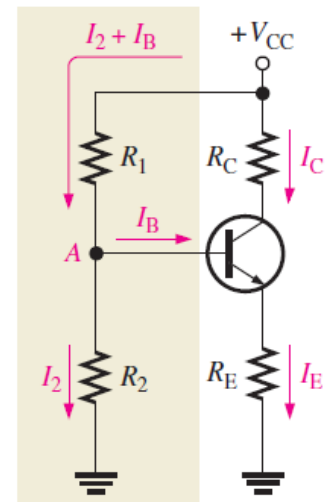


1. Voltage-Divider Bias

A more practical bias method is to use V_{CC} as the single bias source, as shown in Figure. To simplify the schematic, the battery symbol is omitted and replaced by a line termination circle with a voltage indicator (V_{CC}) as shown.

A dc bias voltage at the base of the transistor can be developed by a resistive voltage divider that consists of R_1 and R_2 , as shown in Figure.

V_{CC} is the dc collector supply voltage. **Two current paths** are between point **A** and **ground**: one through **R_2** and the other through the **base-emitter junction** of the transistor and R_E .



To analyse a voltage-divider circuit in which I_B is small compared to I_2 , first calculate the voltage on the base using the unloaded voltage-divider rule:

$$V_B \cong \left(\frac{R_2}{R_1 + R_2} \right) V_{CC}$$

Once you know the base voltage, you can find the voltages and currents in the circuit, as follows:

$$V_E = V_B - V_{BE}$$

and

$$I_C \cong I_E = \frac{V_E}{R_E}$$

Then,

$$V_C = V_{CC} - I_C R_C$$

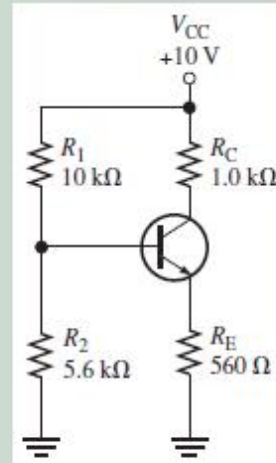
Once you know V_C and V_E , you can determine V_{CE} :

$$V_{CE} = V_C - V_E$$

EXAMPLE 5-2

Determine V_{CE} and I_C in the stiff voltage-divider biased transistor circuit of Figure 5-10 if $\beta_{DC} = 100$.

► FIGURE 5-10



Solution The base voltage is

$$V_B \cong \left(\frac{R_2}{R_1 + R_2} \right) V_{CC} = \left(\frac{5.6 \text{ k}\Omega}{15.6 \text{ k}\Omega} \right) 10 \text{ V} = 3.59 \text{ V}$$

So,

$$V_E = V_B - V_{BE} = 3.59 \text{ V} - 0.7 \text{ V} = 2.89 \text{ V}$$

and

$$I_E = \frac{V_E}{R_E} = \frac{2.89 \text{ V}}{560 \Omega} = 5.16 \text{ mA}$$

Therefore,

$$I_C \cong I_E = 5.16 \text{ mA}$$

and

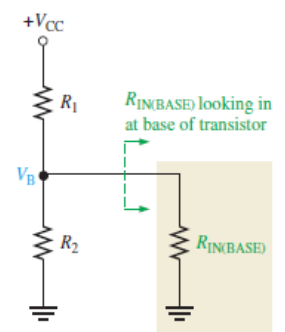
$$V_C = V_{CC} - I_C R_C = 10 \text{ V} - (5.16 \text{ mA})(1.0 \text{ k}\Omega) = 4.84 \text{ V}$$

$$V_{CE} = V_C - V_E = 4.84 \text{ V} - 2.89 \text{ V} = 1.95 \text{ V}$$

Related Problem If the voltage divider in Figure 5-10 was not stiff, how would V_B be affected?

DC Input Resistance at the Transistor Base The dc input resistance of the transistor is proportional to β_{DC} , so it will change for different transistors.

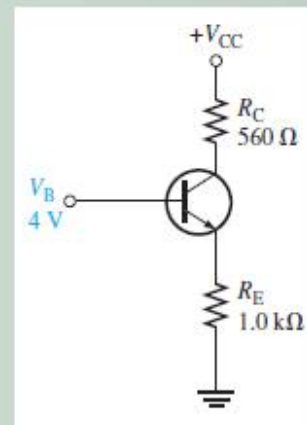
$$R_{IN(BASE)} = \frac{\beta_{DC} V_B}{I_E}$$



EXAMPLE 5-3

Determine the dc input resistance looking in at the base of the transistor in Figure 5-12. $\beta_{DC} = 125$ and $V_B = 4$ V.

► FIGURE 5-12



Solution

$$I_E = \frac{V_B - 0.7 \text{ V}}{R_E} = \frac{3.3 \text{ V}}{1.0 \text{ k}\Omega} = 3.3 \text{ mA}$$

$$R_{IN(BASE)} = \frac{\beta_{DC} V_B}{I_E} = \frac{125(4 \text{ V})}{3.3 \text{ mA}} = 152 \text{ k}\Omega$$

Related Problem What is $R_{IN(BASE)}$ in Figure 5-12 if $\beta_{DC} = 60$ and $V_B = 2$ V?

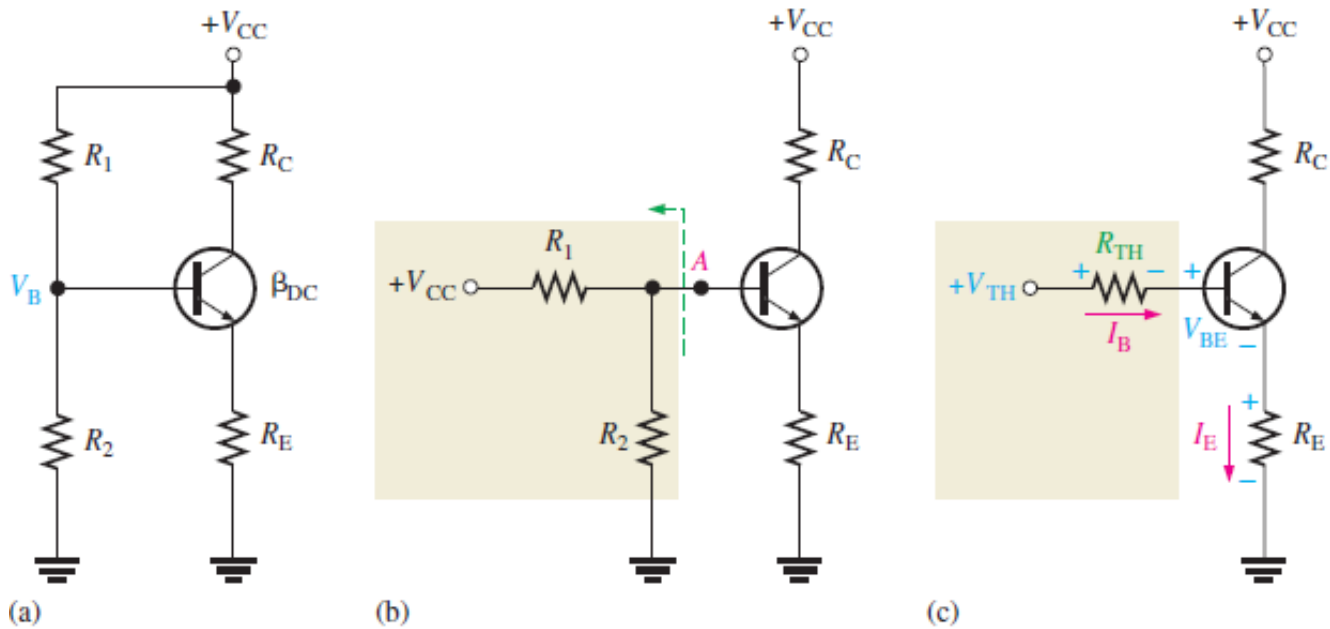
2. Thevenin's Theorem Applied to Voltage-Divider Bias

To analyse a voltage-divider biased transistor circuit for base current loading effects, we will apply Thevenin's theorem to evaluate the circuit.

$$V_{TH} = \left(\frac{R_2}{R_1 + R_2} \right) V_{CC}$$

and the resistance is

$$R_{TH} = \frac{R_1 R_2}{R_1 + R_2}$$



$$V_{TH} - V_{R_{TH}} - V_{BE} - V_{R_E} = 0$$

Substituting, using Ohm's law, and solving for V_{TH} ,

$$V_{TH} = I_B R_{TH} + V_{BE} + I_E R_E$$

Substituting I_E / β_{DC} for I_B ,

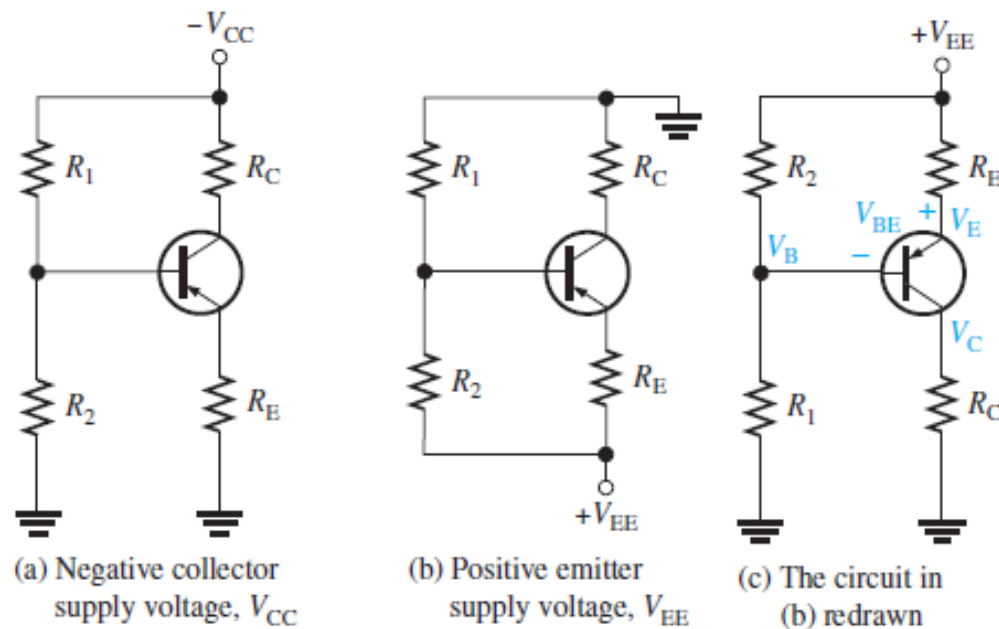
$$V_{TH} = I_E (R_E + R_{TH} / \beta_{DC}) + V_{BE}$$

Then solving for I_E ,

$$I_E = \frac{V_{TH} - V_{BE}}{R_E + R_{TH} / \beta_{DC}}$$

3. Voltage-Divider Biased PNP Transistor

*pn*p transistor requires bias polarities opposite to the *n*p*n*. This can be accomplished with a negative collector supply voltage, as in Figure (a), or with a positive emitter supply voltage, as in Figure (b).



In a schematic, the *pn*p is often drawn upside down so that the supply voltage is at the top of the schematic and ground at the bottom, as in Figure (c).

$$V_{TH} + I_B R_{TH} - V_{BE} + I_E R_E = 0$$

By Thevenin's theorem,

$$V_{TH} = \left(\frac{R_2}{R_1 + R_2} \right) V_{CC}$$

$$R_{TH} = \frac{R_1 R_2}{R_1 + R_2}$$

The base current is

$$I_B = \frac{I_E}{\beta_{DC}}$$

The equation for I_E is

$$I_E = \frac{-V_{TH} + V_{BE}}{R_E + R_{TH}/\beta_{DC}}$$

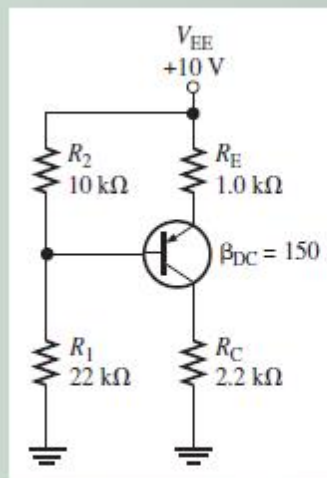
The equation for I_E is

$$I_E = \frac{V_{TH} + V_{BE} - V_{EE}}{R_E + R_{TH}/\beta_{DC}}$$

EXAMPLE 5-4

Find I_C and V_{EC} for the *pn*p transistor circuit in Figure 5-15.

► FIGURE 5-15



Solution This circuit has the configuration of Figures 5-14(b) and (c). Apply Thevenin's theorem.

$$V_{TH} = \left(\frac{R_1}{R_1 + R_2} \right) V_{EE} = \left(\frac{22 \text{ k}\Omega}{22 \text{ k}\Omega + 10 \text{ k}\Omega} \right) 10 \text{ V} = (0.688) 10 \text{ V} = 6.88 \text{ V}$$

$$R_{TH} = \frac{R_1 R_2}{R_1 + R_2} = \frac{(22 \text{ k}\Omega)(10 \text{ k}\Omega)}{22 \text{ k}\Omega + 10 \text{ k}\Omega} = 6.88 \text{ k}\Omega$$

Use Equation 5-8 to determine I_E .

$$I_E = \frac{V_{TH} + V_{BE} - V_{EE}}{R_E + R_{TH}/\beta_{DC}} = \frac{6.88 \text{ V} + 0.7 \text{ V} - 10 \text{ V}}{1.0 \text{ k}\Omega + 45.9 \Omega} = \frac{-2.42 \text{ V}}{1.0459 \text{ k}\Omega} = -2.31 \text{ mA}$$

The negative sign on I_E indicates that the assumed current direction in the Kirchhoff's analysis is opposite from the actual current direction. From I_E , you can determine I_C and V_{EC} as follows:

$$I_C = I_E = 2.31 \text{ mA}$$

$$V_C = I_C R_C = (2.31 \text{ mA})(2.2 \text{ k}\Omega) = 5.08 \text{ V}$$

$$V_E = V_{EE} - I_E R_E = 10 \text{ V} - (2.31 \text{ mA})(1.0 \text{ k}\Omega) = 7.68 \text{ V}$$

$$V_{EC} = V_E - V_C = 7.68 \text{ V} - 5.08 \text{ V} = 2.6 \text{ V}$$



EXAMPLE 5-5

Find I_C and V_{CE} for a *pn*p transistor circuit with these values: $R_1 = 68 \text{ k}\Omega$, $R_2 = 47 \text{ k}\Omega$, $R_C = 1.8 \text{ k}\Omega$, $R_E = 2.2 \text{ k}\Omega$, $V_{CC} = -6 \text{ V}$, and $\beta_{DC} = 75$. Refer to Figure 5-14(a), which shows the schematic with a negative supply voltage.

Solution Apply Thevenin's theorem.

$$\begin{aligned} V_{TH} &= \left(\frac{R_2}{R_1 + R_2} \right) V_{CC} = \left(\frac{47 \text{ k}\Omega}{68 \text{ k}\Omega + 47 \text{ k}\Omega} \right) (-6 \text{ V}) \\ &= (0.409)(-6 \text{ V}) = -2.45 \text{ V} \end{aligned}$$

$$R_{TH} = \frac{R_1 R_2}{R_1 + R_2} = \frac{(68 \text{ k}\Omega)(47 \text{ k}\Omega)}{(68 \text{ k}\Omega + 47 \text{ k}\Omega)} = 27.8 \text{ k}\Omega$$

Use Equation 5-7 to determine I_E .

$$\begin{aligned} I_E &= \frac{-V_{TH} + V_{BE}}{R_E + R_{TH}/\beta_{DC}} = \frac{2.45 \text{ V} + 0.7 \text{ V}}{2.2 \text{ k}\Omega + 371 \Omega} \\ &= \frac{3.15 \text{ V}}{2.57 \text{ k}\Omega} = 1.23 \text{ mA} \end{aligned}$$

From I_E , you can determine I_C and V_{CE} as follows:

$$I_C = I_E = 1.23 \text{ mA}$$

$$V_C = -V_{CC} + I_C R_C = -6 \text{ V} + (1.23 \text{ mA})(1.8 \text{ k}\Omega) = -3.79 \text{ V}$$

$$V_E = -I_E R_E = -(1.23 \text{ mA})(2.2 \text{ k}\Omega) = -2.71 \text{ V}$$

$$V_{CE} = V_C - V_E = -3.79 \text{ V} + 2.71 \text{ V} = -1.08 \text{ V}$$